

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMEX.186DV1APPLICATION NO.
UnknownINFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Raaijmakers et al.FILING DATE
HerewithGROUP
Unknown

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09/764,711
01/18/01

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
AM	3,900,597	08/19/75	Chruma et al.			
	4,062,707	12/13/77	Mochizuki et al.			
	4,217,374	08/12/80	Ovshinsky et al.			
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						YES	NO
AK	51-1389 ✓	1976	Japan			Yes	
AK	54-4066 ✓	1979	Japan			Yes	
AK	60-36662 ✓	1985	Japan			Yes	
AK	63-3414 ✓	1986	Japan			Yes	
AK	63-239811 ✓		Japan			Yes	
AK	63-258016 ✓		Japan				
AK	2-119223 ✓	1990	Japan				
AK	2-122076 ✓	1990	Japan			Yes	
AK	2-208293 ✓		Japan			Yes	

EXAMINER
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OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

AK	✓ Bloem, J. "High Chemical Vapour Deposition Rates of Epitaxial Silicon Layers", J. of Crystal Growth, Vol. 18, 1973, pp. 70-76. ✓
	✓ Bunshah et al. "Deposition Technologies for Films and Coatings; Developments and Applications," Noyes Publications, 1982, p. 357. ✓
	✓ Claasen et al., "The Deposition Of Silicon From Silane In a Low-Pressure Hot-Wall System", J. of Crystal Growth, Vol. 57, 1982, pp. 259-266. ✓
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	✓ C.R. Kleijn, "A Mathematical Model of the Hydrodynamics and Gas-Phase Reactions in Silicon LPCVD in a Single-Wafer Reactor," J. Electrochem Soc., Vol 138, No. 7, July 1991, pp. 1190-1200.

EXAMINER

DATE CONSIDERED

12/3/01

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.